

*SUB  
C27*

35. Integrated circuitry comprising:

a semiconductive substrate having an outer surface;  
an inner conductive core spaced from and suspended over the outer  
surface;

*B2*  
a polymer dielectric layer surrounding a substantial portion of the inner  
conductive core; and

an outer conductive sheath surrounding a substantial portion of the  
polymer dielectric layer.

36. Integrated circuitry comprising:

a semiconductive substrate having an outer surface;  
a pair of spaced-apart terminal members disposed over the outer  
surface and extending elevationally away therefrom;

an inner conductive core operably connected with and suspended  
between the spaced-apart terminal members above the outer surface;

a polymer dielectric layer over a substantial portion of the inner  
conductive core; and

an outer conductive sheath surrounding a substantial portion of the  
polymer dielectric layer.

*Sub C2*

37. Integrated circuitry comprising:

a substrate having an outer surface;

a pair of upstanding, spaced-apart conductive terminal members disposed over the substrate outer surface;

*B2*

a copper-comprising layer of material operably connected with and suspended above the outer surface between the terminal members, the copper-comprising layer having a thickness of between about 100 to 200 nanometers;

a conductive layer of material disposed over and operably connected with the copper-comprising layer of material, the conductive layer comprising conductive material selected from the group consisting of copper, gold, nickel, cobalt, and iron;

a dielectric layer comprising parylene disposed over the conductive layer of material, the dielectric layer surrounding conductive layer portions which extend between the terminal members; and

an outer conductive sheath of material disposed over the dielectric layer and surrounding dielectric layer portions which extend between the terminal members.

38. The integrated circuitry of claim 35, wherein the outer conductive sheath leaves some void space between the outer conductive sheath and the outer surface.

*C*

39. The integrated circuitry of claim 35, wherein the outer conductive sheath is not formed ~~on~~ the outer surface.

*SUB C37* 40. The integrated circuitry of claim 35, wherein the polymer dielectric layer comprises parylene.

*P2* 41. The integrated circuitry of claim 35, wherein the polymer dielectric layer has a relative dielectric constant of about 2.6.

42. The integrated circuitry of claim 35, wherein the outer conductive sheath comprises aluminum.

43. The integrated circuitry of claim 35, wherein the inner conductive core comprises copper.

44. The integrated circuitry of claim 35, wherein the inner conductive core comprises a material chosen from a group consisting of nickel, cobalt and iron.

45. The integrated circuitry of claim 36, wherein the polymer dielectric layer comprises parylene.

SUB C3

46. The integrated circuitry of claim 36, wherein the polymer dielectric layer has a relative dielectric constant of about 2.6.

B2

47. The integrated circuitry of claim 36, wherein the outer conductive sheath comprises aluminum.

48. The integrated circuitry of claim 36, wherein the inner conductive core comprises copper.

49. The integrated circuitry of claim 36, wherein the inner conductive core comprises a material chosen from a group consisting of nickel, cobalt and iron.

50. Integrated circuitry comprising:  
a semiconductive substrate having an outer surface;  
an inner conductive core spaced from and over the outer surface;  
a polymer dielectric layer surrounding a substantial portion of the suspended inner conductive core; and  
an outer conductive sheath surrounding a substantial portion of the polymer dielectric layer, the outer conductive sheath leaving some void space between the outer conductive sheath and the outer surface, wherein the outer conductive sheath is not formed on the outer surface.

*SUB  
C3*

51. The integrated circuitry of claim 50, wherein the polymer dielectric layer comprises parylene.
- P2* 52. The integrated circuitry of claim 50, wherein the polymer dielectric layer has a relative dielectric constant of about 2.6.
53. The integrated circuitry of claim 50, wherein the outer conductive sheath comprises aluminum.
54. The integrated circuitry of claim 50, wherein the inner conductive core comprises copper.
55. The integrated circuitry of claim 50, wherein the inner conductive core comprises a material chosen from a group consisting of nickel, cobalt and iron.

*SUB  
C3*

56. Integrated circuitry comprising:  
a semiconductive substrate having an outer surface;  
a pair of spaced-apart terminal members disposed over the outer  
surface and extending elevationally away therefrom;  
*B2*  
an inner conductive core operably connected with and suspended  
between the spaced-apart terminal members above the outer surface;  
a polymer dielectric layer surrounding the suspended inner conductive  
core; and  
an outer conductive sheath surrounding a substantial portion of the  
polymer dielectric layer while some void space is present between the  
dielectric layer over the suspended inner conductive core and the outer  
surface, the outer conductive sheath leaving some void space between the  
outer conductive sheath and the outer surface, wherein the outer conductive  
sheath is not formed over the substrate outer surface.

57. The integrated circuitry of claim 56, wherein the polymer dielectric  
layer comprises parylene.

58. The integrated circuitry of claim 56, wherein the polymer dielectric  
layer has a relative dielectric constant of about 2.6.

59. The integrated circuitry of claim 56, wherein the outer conductive  
sheath comprises aluminum.

*Sub C3*

60. The integrated circuitry of claim 56, wherein the inner conductive core comprises copper.

*B2*

61. The integrated circuitry of claim 56, wherein the inner conductive core comprises a material chosen from a group consisting of nickel, cobalt and iron.

*SUB  
C3*

62 Integrated circuitry comprising:  
a substrate having an outer surface;  
a pair of upstanding, spaced-apart conductive terminal members disposed over the substrate outer surface;  
a copper-comprising layer of material operably connected with and suspended above the outer surface between the terminal members, the copper-comprising layer having a thickness of between about 100 to 200 nanometers;  
a conductive layer of material operably connected with the copper-comprising layer of material and suspended above the outer surface between the terminal members, the conductive layer comprising conductive material selected from the group consisting of copper, gold, nickel, cobalt, and iron;  
a dielectric layer comprising parylene disposed over the conductive layer of material, the dielectric layer surrounding the suspended conductive layer portions; and  
an outer conductive sheath of material disposed over the dielectric layer and surrounding dielectric layer portions which extend between the terminal members, the outer conductive sheath leaving some void space between the outer conductive sheath and the outer surface, wherein the outer conductive sheath is not formed over the substrate outer surface.